

PCN Number: 20160331001A **PCN Date:** 4/18/2016

Title: Qualification of CFAB as an additional wafer fab site option for select devices in LBC5 process technology

Customer Contact: PCN Manager **Dept:** Quality Services

Proposed 1st Ship Date: 7/8/2016 **Estimated Sample Availability:** Date provided at sample request.

Change Type:		
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>
<input type="checkbox"/>	Design	<input type="checkbox"/>
<input type="checkbox"/>	Test Site	<input type="checkbox"/>
<input type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>
<input checked="" type="checkbox"/>	Wafer Fab Site	<input type="checkbox"/>
<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>
<input type="checkbox"/>	Electrical Specification	<input type="checkbox"/>
<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>
<input type="checkbox"/>	Wafer Bump Material	<input type="checkbox"/>
<input type="checkbox"/>	Wafer Fab Materials	<input type="checkbox"/>
<input type="checkbox"/>	Part number change	

PCN Details

Description of Change:

The purpose of Revision A is to correct/retract devices which may have been inadvertently listed in page 2, but not in the Product Affected Section in page 3.

Please refer to the Product Affected Section on the following:

Group 1: Devices that may appear in notification letter, page 2. These are not affected by this change.

Group 2: This is correct. Original devices listed in Product Affected Section, 4/8/16 notification. These are still affected by this change.

This change notification is to announce the qualification of CFAB as an additional wafer fab site option for the LBC5 devices listed in the product affected section of this document.

Current			Additional		
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
DP1DM5	LBC5	200 mm	CFAB	LBC5	200 mm

The LBC5 process technology has been running successfully in production at CFAB since 2012.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Current			
Chip Sites	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DP1DM5	DM5	USA	Dallas
New			
Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
CFAB	CU3	CHN	Chengdu

Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS

MADE IN: Malaysia
2DC: 20:



(1P) SN74LS07NSR
(Q) 2000 (D) 0336
(31T) LOT: 3959047MLA
(4W) TKY (1T) 7523483SI2
(P)
(2P) REV: (V) 0033317
(20L) CSO: SHE (21L) CCO:USA
(22L) ASO: MLA (23L) ACO: MYS

MSL 2 /260C/1 YEAR SEAL DT
MSL 1 /235C/UNLIM 03/29/04

OPT:
ITEM:
LBL: 5A (L) TO: 1750

Product Affected:

Group 1: Devices that may appear in notification letter, page 2. These are not affected by this change.

TAS5721DCA	TAS5731MPHP	TAS5731PHP	
TAS5721DCAR	TAS5731MPHPR	TAS5731PHPR	

Group 2: This is correct. Original devices listed in Product Affected Section, 4/8/16 notification. These are still affected by this change.

CXD9981TNDDV	TAS5342LAADDVR	TAS5614ADKD	TAS5708PHPR
CXD9981TNDDVR	TAS5352ADDV	TAS5614ADKDR	TAS5710PHP
CXD9981UTNDDV	TAS5352ADDVR	TAS5614APHD	TAS5710PHPR
CXD9981UTNDDVR	TAS5613ADKD	TAS5614APHDR	TPA3251D2DDV
TAS5342ADDV	TAS5613ADKDR	TAS5708LPHP	TPA3251D2DDVR
TAS5342ADDVR	TAS5613APHD	TAS5708LPHPR	TPS65149RSHR
TAS5342LAADDV	TAS5613APHDR	TAS5708PHP	TPS65155RKPR

Qualification Report

**Qualification of LBC5 Process Technology at CFAB
Approved 03/02/2012**

Die Attributes

Attributes	Process QBS : TAS5613APHD Approved: 3/2/2012	Process QBS: DRV8813A0PWP Approved: 3/2/2012	Process QBS: SN8C0183PWP Approved: 3/2/2012
Wafer Fab Site	CFAB	CFAB	CFAB
Wafer Fab Process	LBC5	LBC5	LBC5
Wafer Diameter	200mm	200mm	200mm

- QBS: Qual By Similarity
- Qual Device TAS5613APHD and SN8C0183PWP are qualified at LEVEL3-260C
- Qual Device DRV8813A0PWP is qualified at LEVEL1-260C

Qualification Results
Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: TAS5613APHD	Qual Device: DRV8813A0PWP	Qual Device: SN8C0183PWP
AC	Autoclave 121C	96 Hours	3/77/0	3/77/0	-
ED	Electrical Characterization	Per Datasheet Parameters	3/Pass	3/Pass	3/3/0
HAST	Biased HAST, 130C/85%RH	96 Hours	3/77/0	-	-
HBM	ESD - HBM	1500 V	3/21/0	1/3/0	-
CDM	ESD - CDM	250 V	3/15/0	1/3/0	-
HTOL	Life Test, 155C	240 Hours	3/77/0		3/77/0
HTSL	High Temp Storage Bake 170C	420 Hours	3/77/0	-	-
LU	Latch-up	(per JESD78)	3/6/0	1/6/0	-
TC	Temperature Cycle, -65/150C	500 Cycles	3/77/0	3/77/0	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com